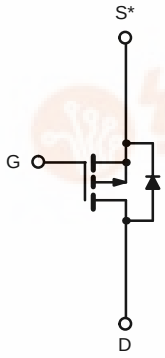
P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.015 @ V_{GS} = -4.5 V	-7.4
	0.020 @ V_{GS} = -2.5 V	- 6.3
	0.027 @ V_{GS} = -1.8 V	- 5.5

TrenchFET® Power MOSFETs

TSSOP-8

Top View



P-Channel MOSFET

* Source Pins 2, 3, 6 and 7 must be tied common.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	-20		V
Gate-Source Voltage		V_{GS}	±8		
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	- 7.4	-6.2	A
	T_A = 70°C		-5.9	4.9	
Pulsed Drain Current (10 µs Pulse Width)		I_{DM}	-30		
Continuous Source Current (Diode Conduction)[a]		I_S	-1.35	-0.95	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	1.5	1.05	W
	T_A = 70°C		1.0	0.67	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	65	83	°C/W
	Steady State		100	120	
Maximum Junction-to-Foot	Steady State	R_{thJF}	46	56	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

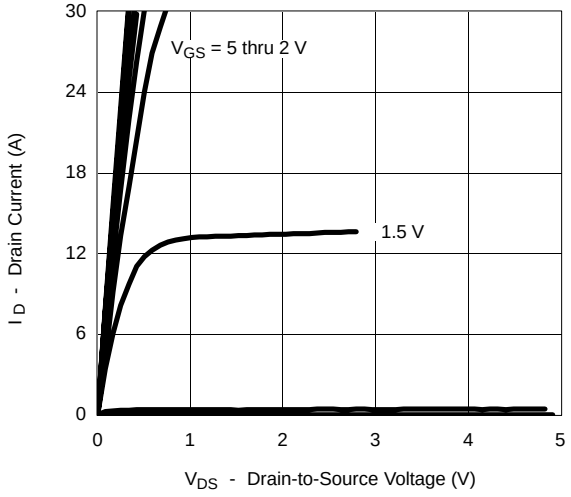
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-0.45		-0.8	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -16 V, V_{GS} = 0 V			-1	µA
		V_{DS} = -16 V, V_{GS} = 0 V, T_J = 70°C			-10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} -5 V, V_{GS} = -4.5 V	20			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = -4.5 V, I_D = -7.4 A		0.011	0.015	Ω
		V_{GS} = -2.5 V, I_D = -6.3 A		0.015	0.020	
		V_{GS} = -1.8 V, I_D = -5.5 A		0.020	0.027	Ω
Forward Transconductance[a]	g_{fs}	V_{DS} = -15 V, I_D = -7.4 A		34		S
Diode Forward Voltage[a]	V_{SD}	I_S = -1.3 A, V_{GS} = 0 V		-0.64	-1.1	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = -10 V, V_{GS} = -5 V, I_D = -7.4 A		40	60	nC
Gate-Source Charge	Q_{gs}			5.2		
Gate-Drain Charge	Q_{gd}			8		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 15 Ω I_D ≅ -1 A, V_{GEN} = -4.5 V, R_G = 6 Ω		35	55	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			190	300	
Fall Time	t_f			90	150	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = -1.3 A, di/dt = 100 A/µs		75	120	

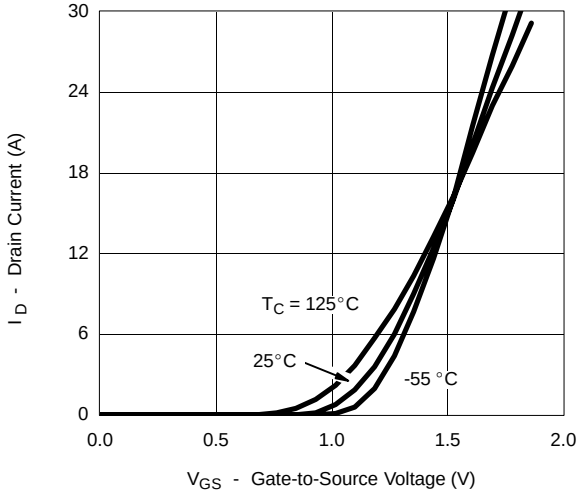
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Output Characteristics

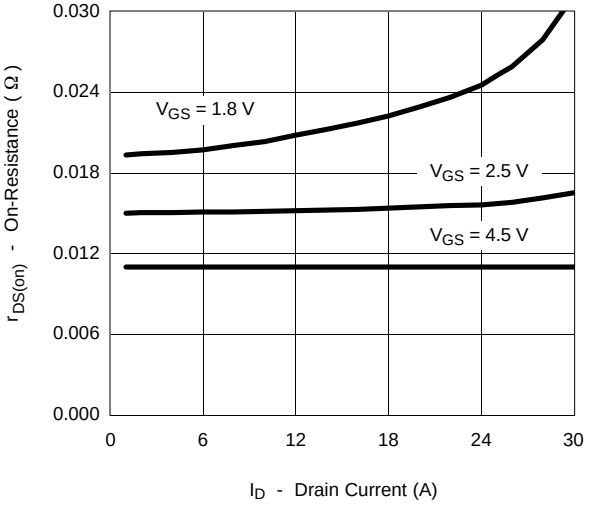


Transfer Characteristics

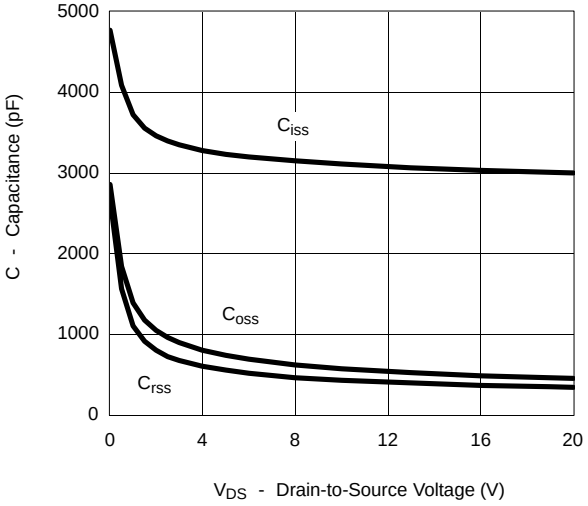


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

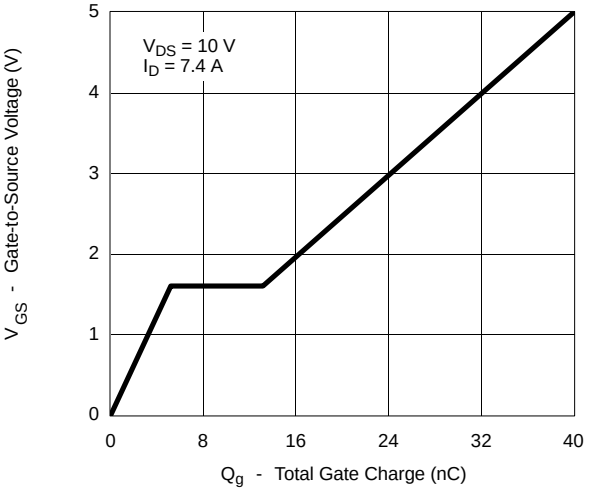
On-Resistance vs. Drain Current



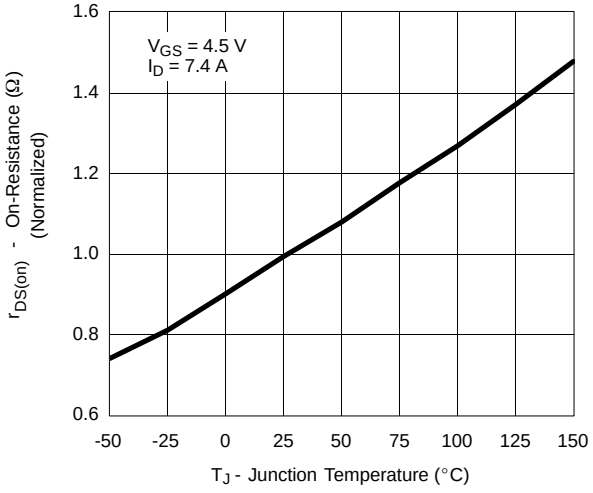
Capacitance



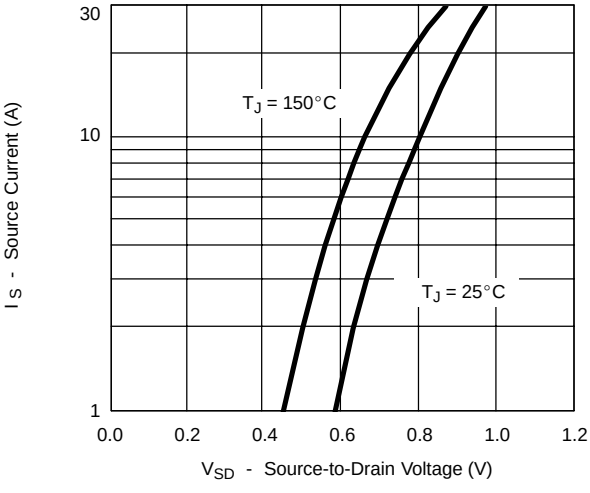
Gate Charge



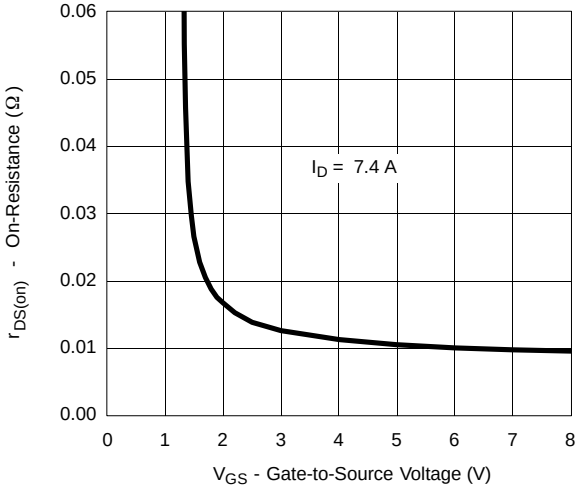
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

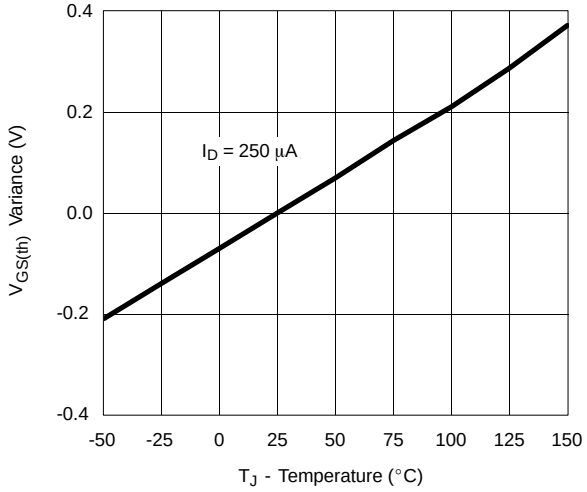


On-Resistance vs. Gate-to-Source Voltage

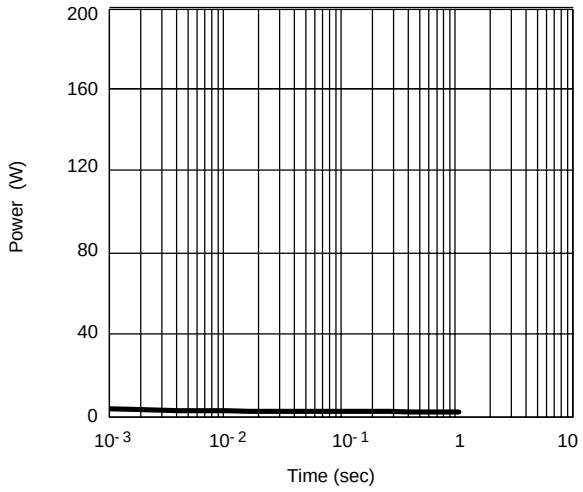


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

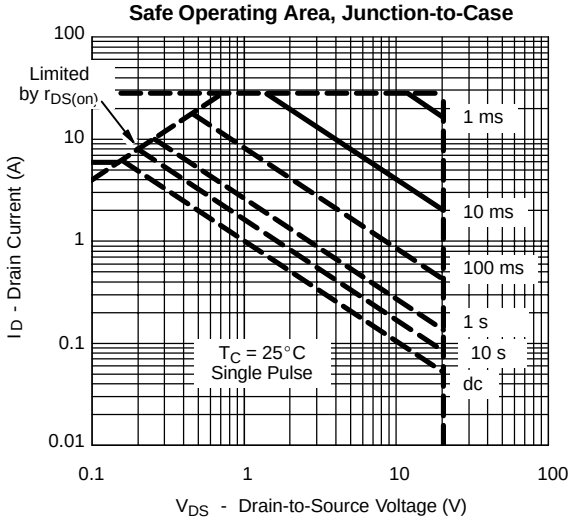
Threshold Voltage



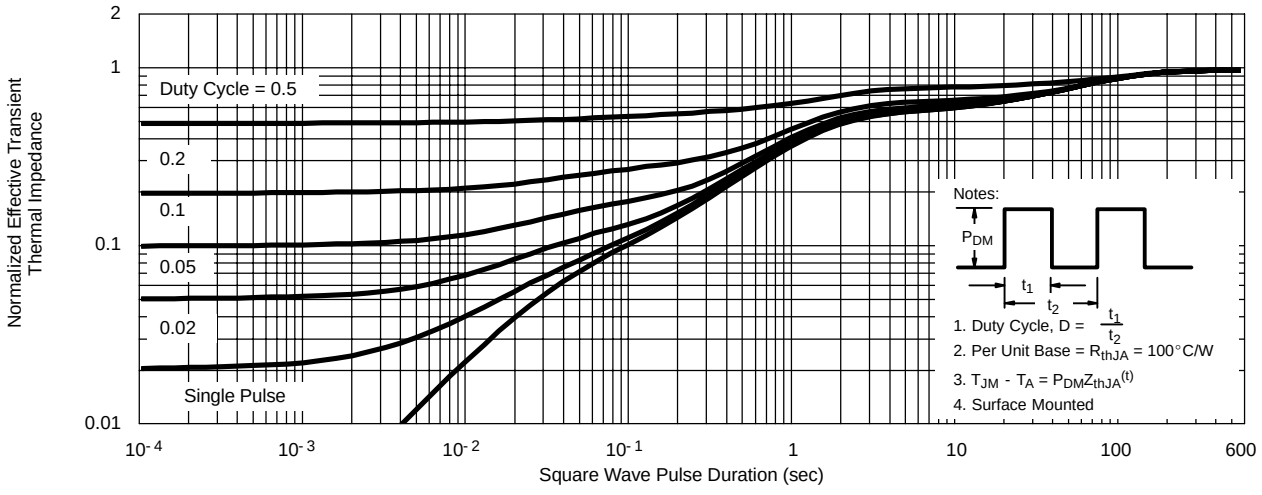
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Normalized Thermal Transient Impedance, Junction-to-Foot